

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: **HORI, et al.**

Serial No.: **10/662,384**

Filed: **September 16, 2003**



Group Art Unit: **UNASSIGNED**

Examiner: **UNASSIGNED**

For: **SEMICONDUCTOR DEVICE, MANUFACTURE AND EVALUATION METHODS FOR SEMICONDUCTOR DEVICE, AND PROCESS CONDITION EVALUATION METHOD**

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)(4)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

November 12, 2003

Sir:

The attention of the Patent and Trademark Office is hereby directed to the document listed on the attached Form PTO-1449. One copy of this document is attached.

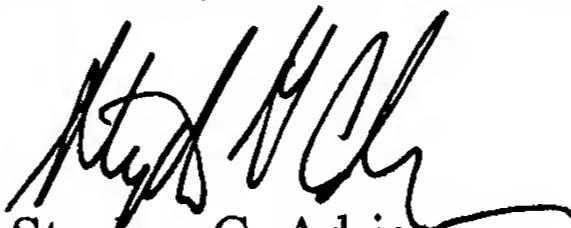
No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the issuance of a first official action on the merits in the above-identified patent application.

The above information is presented so that the Patent and Trademark Office can, in the first instance, determine any materiality thereof to the claimed invention. See 37 CFR 1.104(a) concerning the PTO duty to consider and use any such information. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the documents cited in the attached Form PTO-1449 be made of record therein and appear on the first page of any patent to issue therefrom.

The Commissioner is authorized to charge our Deposit Account No. 50-2866 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,

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Enclosures: PTO-1449 and 1 reference

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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 031111	Serial No. 10/662,384
	Applicant(s): HORI, et al.	
	Filing Date: September 16, 2003	Group Art Unit: Unassigned

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA					
_____	AB					
_____	AC					
_____	AD					
_____	AE					

FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)
_____	AF			
_____	AG			
_____	AH			
_____	AI			
_____	AJ			

OTHER DOCUMENTS

_____	A K AL	Chen et al., Downscaling Limit of Equivalent Oxide Thickness in Formation of Ultrathin Gate Dielectric by Thermal-Enhanced Remote Plasma Nitridation, IEEE TRANSACTIONS ON ELECTRON DEVICES, May 2002, Vol. 49, No.5, P,840-845
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Examiner

Date Considered